

# Electronic Supplementary Information

## Silk-Derived Carbon Nanosheets for Transparent Conducting Electrodes on Flexible Substrates

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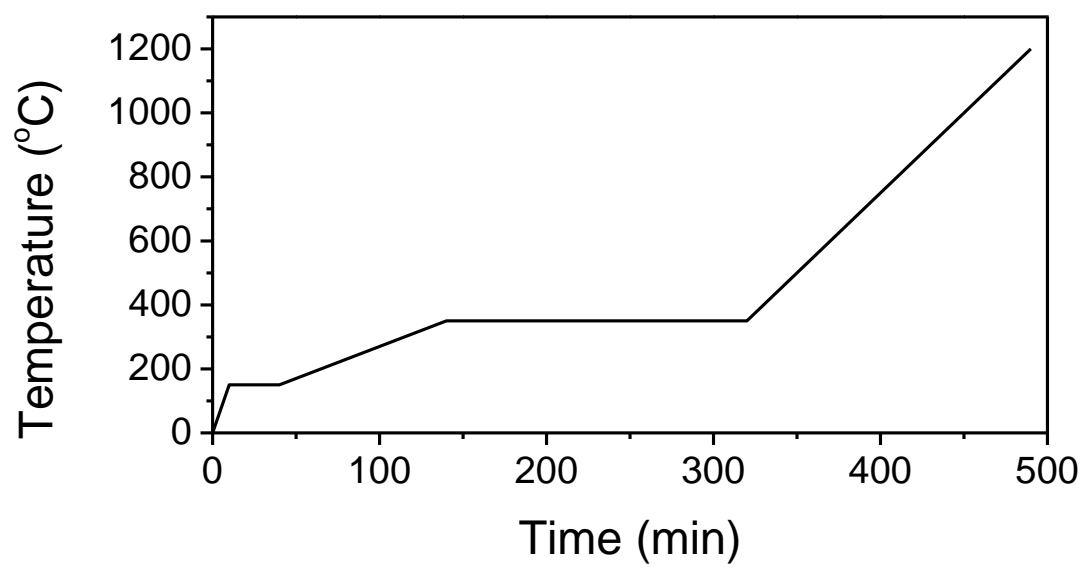
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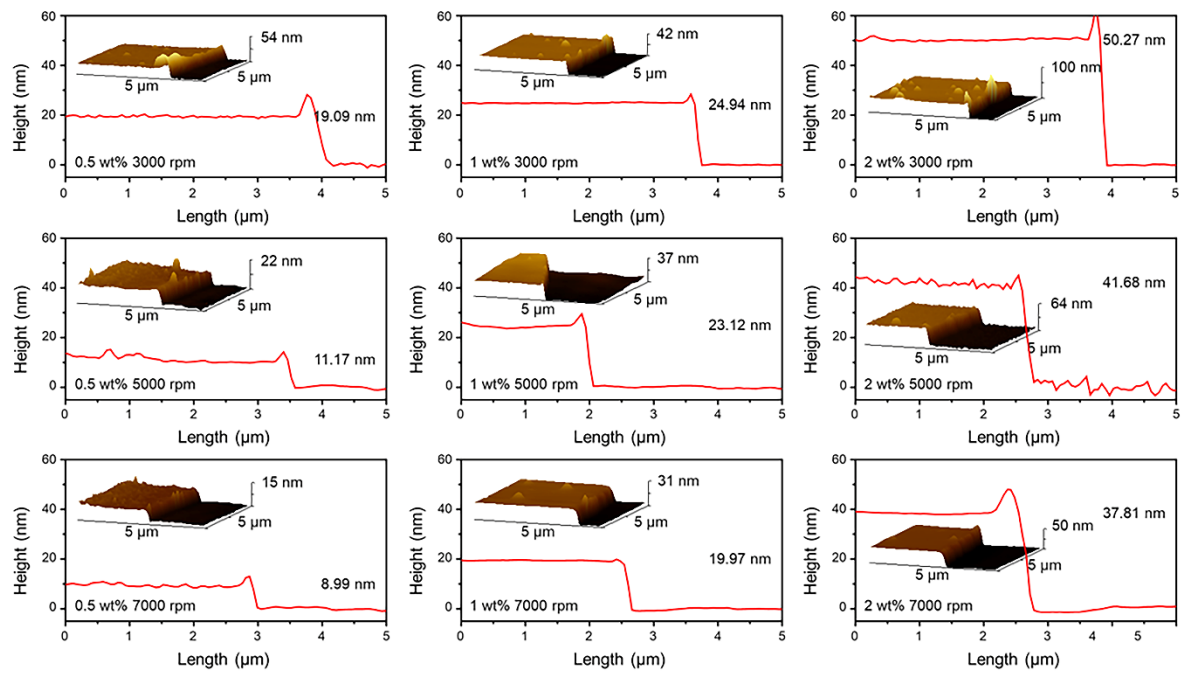
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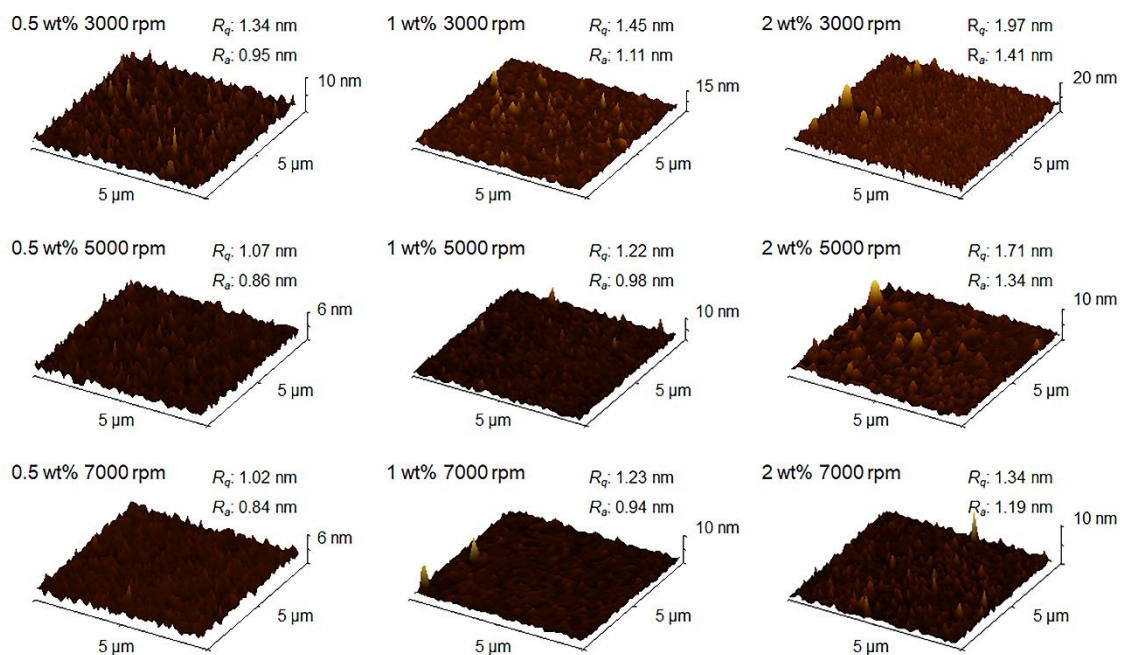
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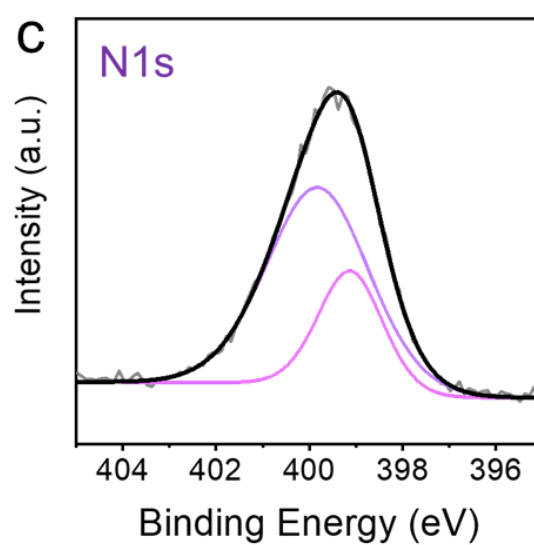
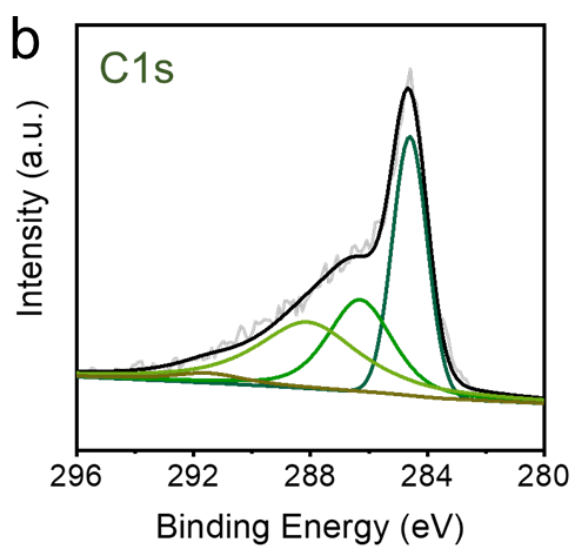
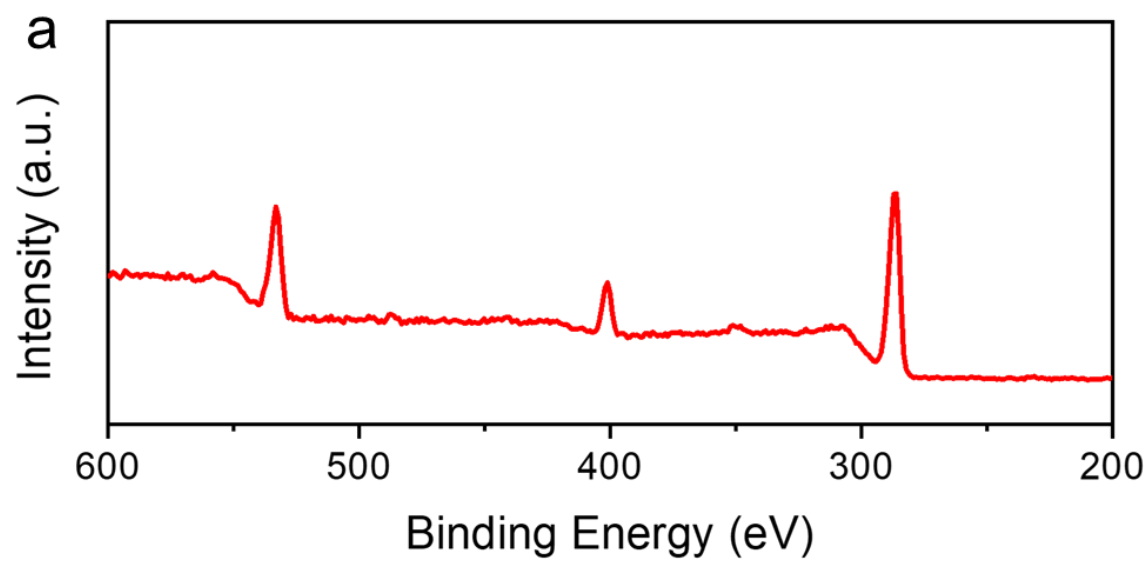
**Figure S1.** Temperature schedule of carbonization process for silk fibroin-based carbon nanosheets.



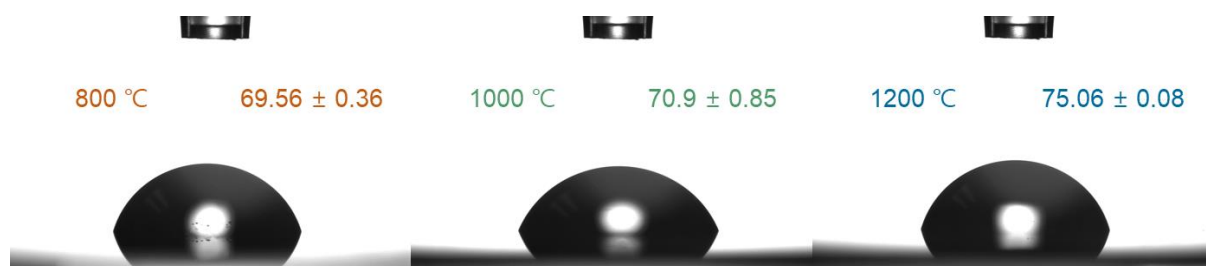
**Figure S2.** AFM images showing thickness dependence of the silk fibroin thin film on the spin rates and the concentrations of silk fibroin.



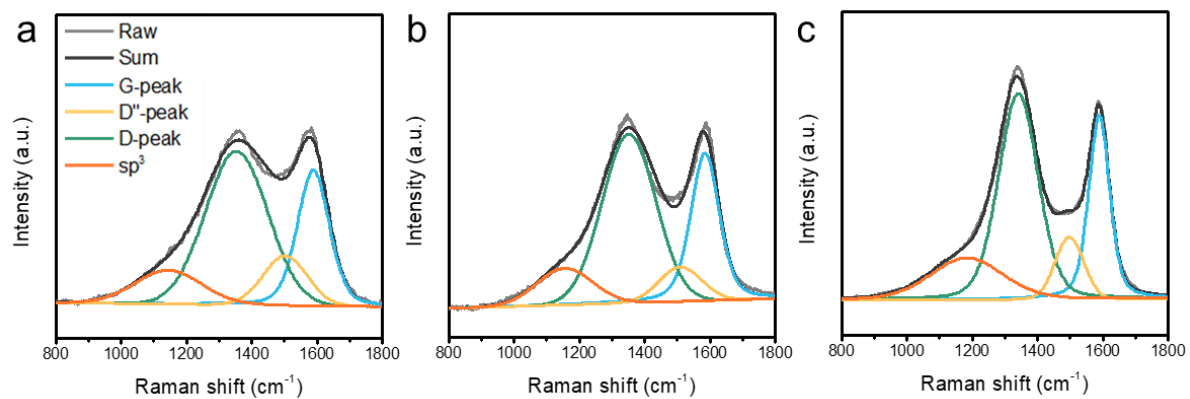
**Figure S3.** 3D AFM topography images showing the surface roughness of silk fibroin films prepared at different solution concentrations (0.5–2.0 wt.%) and spin-coating speeds (1000–7000 rpm).  $R_a$  values correspond to  $5 \times 5 \mu\text{m}$  scan areas on  $\text{SiO}_2/\text{Si}$  substrates.



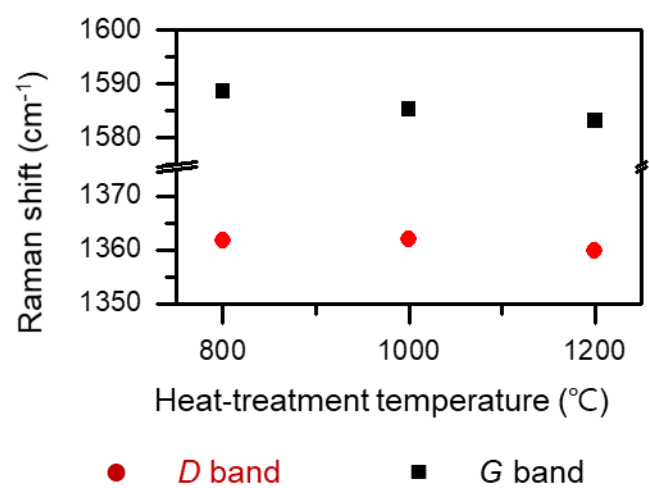
**Figure S4.** (a) XPS survey spectra of regenerated silk fibroin, and deconvoluted high-resolution spectra of (b) C1s and (c) N1s.



**Figure S5.** Contact angle of a water droplet on the surface of silk fibroin-derived carbon nanosheets prepared with different temperature.

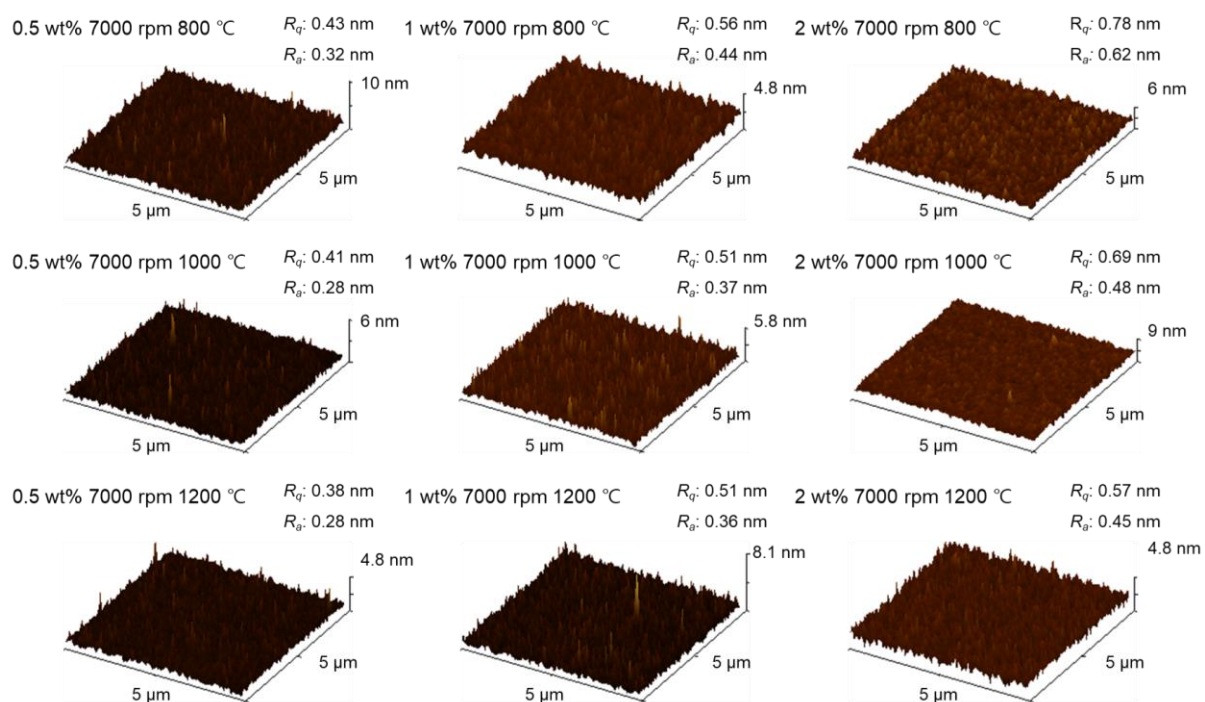


**Figure S6.** Deconvoluted Raman spectra of SF-derived carbon nanosheets heat-treated at (a) 800 °C, (b) 1,000 °C, and (c) 1,200 °C.

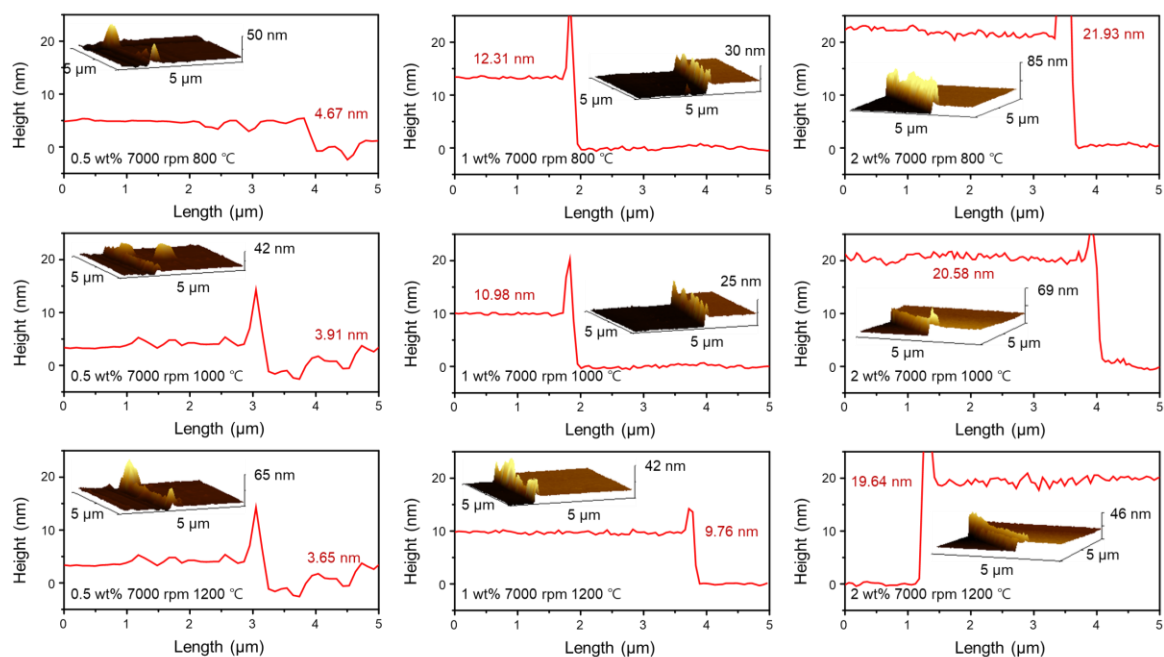


**Figure S7.** Position of *D* and *G* bands of silk fibroin-based CNs according to heat-treatment temperature.





**Figure S8.** Surface roughness of silk fibroin-derived carbon nanosheet films with different concentration and HTT.



**Figure S9.** AFM images and thickness of carbonized silk fibroin thin films prepared using different concentration and HTT

**Table S1.** Elemental composition and chemical structure of regenerated SF by XPS Analysis

Element	Binding Energy	Assignment	Atomic Fraction by XPS	Atomic Fraction by theoretical Calculation*
C 1s	284.6 eV	C-C, C-H	0.64	0.55
	285.9 eV	C-N		
	288.2 eV	O=C-N		
O 1s	531.0 eV	O in amide	0.21	0.24
N 1s	398.50 eV	N in amide	0.15	0.21

\*Data calculated from the 10 main amino acid residue (Gly, Ala, Ser, Try, Val, Asp/Asn, Thr Glu/Gln, Phe, and lie) known as comprising 98.1% of the total composition of silk fibroin

**Table S1.** Comparison of representative carbon-based transparent conductive films, including graphene-, CNT-, and polymer-derived carbon nanosheets, highlighting their transmittance at 550 nm and sheet resistance values

Material	Transmittance @ 550 nm (%)	Sheet Resistance ( $\Omega/\text{sq}$ )	Ref.
single-layer graphene film	89.0~96.5	300~11200	S1
bilayer graphene film	83.0~94.7	180~500	S1
graphene/polymer nanocomposite	>90	~15	S2
carbon-welded SWCNT	>90	41	S3
CNT–PAA hybrid	91/84	150/60	S4
polyimide-derived CNSs	54~89	1600~14700	S5
polyethylene-derived CNSs	80~90	$10^2\sim 10^3$	S6
Nitrogen-containing oligomers		100-2000	S7
PAN-derived CNSs	80~90	$10^2\sim 10^3$	S8
CNS from silk (this work)	>98	$\sim 10^2$	This work

## References

- S1. S. Lee, K. Lee, C. H. Liu, and Z. Zhong, *Nanoscale*, 2012, 4(2), 639-644.
- S2. C. Biswas, I. Candan, Y. Alaskar, H. Qasem, W. Zhang, A. Z. Stieg, Y.-H. Xiw, and K. L. Wang, *Sci. rep.*, 2018, 8, 10259.
- S3. S. Jiang, P. X. Hou, M. L. Chen, B. W. Wang, D. M. Sun, D. M. Tang, Q. Jin, Q.-X. Guo, D.-D. Zhang, K.-P. Tai, J. Tan, E. O. Kauppinen, C. Lui, and H.-M. Cheng, *Sci. adv.*, 2018, 4(5), eaap9264.
- S4. Y. Zhou, R. Azumi, and S. Shimada, *Nanoscale*, 2019, 11(9), 3804-3813.
- S5. G. Souri, S. J. Yu, H. Yeo, M. Goh, J.-Y. Hwang, S. M. Kim, B.-C. Ku, Y. G. Jeong, and N.-H. You, *RSC Adv.*, 2016, 6(58), 52509-52517.
- S6. M. Yi, M. Han, J. Chen, Z. Hao, Y. Chen, Y. Yao, and R. Sun, *Nanomaterials*, 2021, 12(1), 111.
- S7. K. K. Chung, N. Fechner, M. Patrini, P. Galinetto, D. Comoretto, and M. Antonietti, *Carbon*, 2015, 94, 1044-1051.
- S8. S. I. Na, Y. J. Noh, S. Y. Son, T. W. Kim, S. S. Kim, S. Lee, and H. I. Joh, *Appl. Phys. Lett.*, 2013, 102(4).